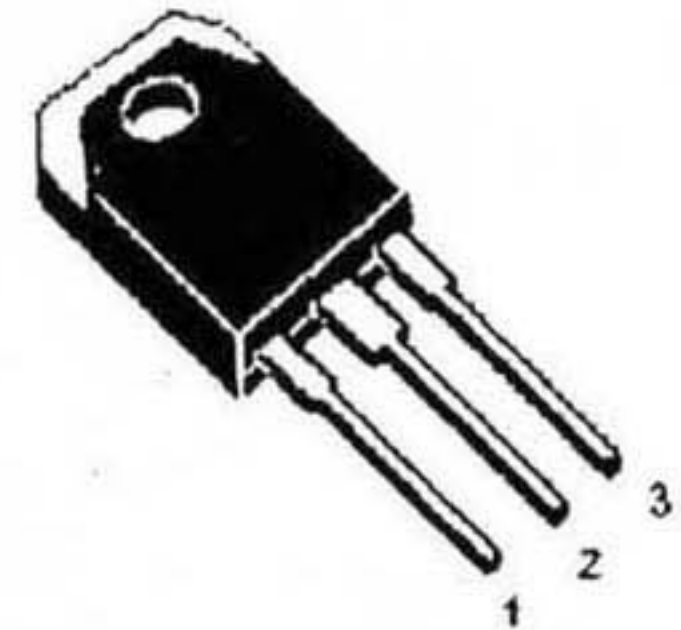


## TO-3PN Plastic-Encapsulate Transistors

**D4515** TRANSISTOR(NPN)

## ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	VCBO	700	V
Collector-Emitter Voltage	VCEO	400	V
Emitter-Base voltage	VEBO	9	V
Collector Current	Ic	15	A
Collector Power Dissipation	Pc	120	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C



TO-3PN

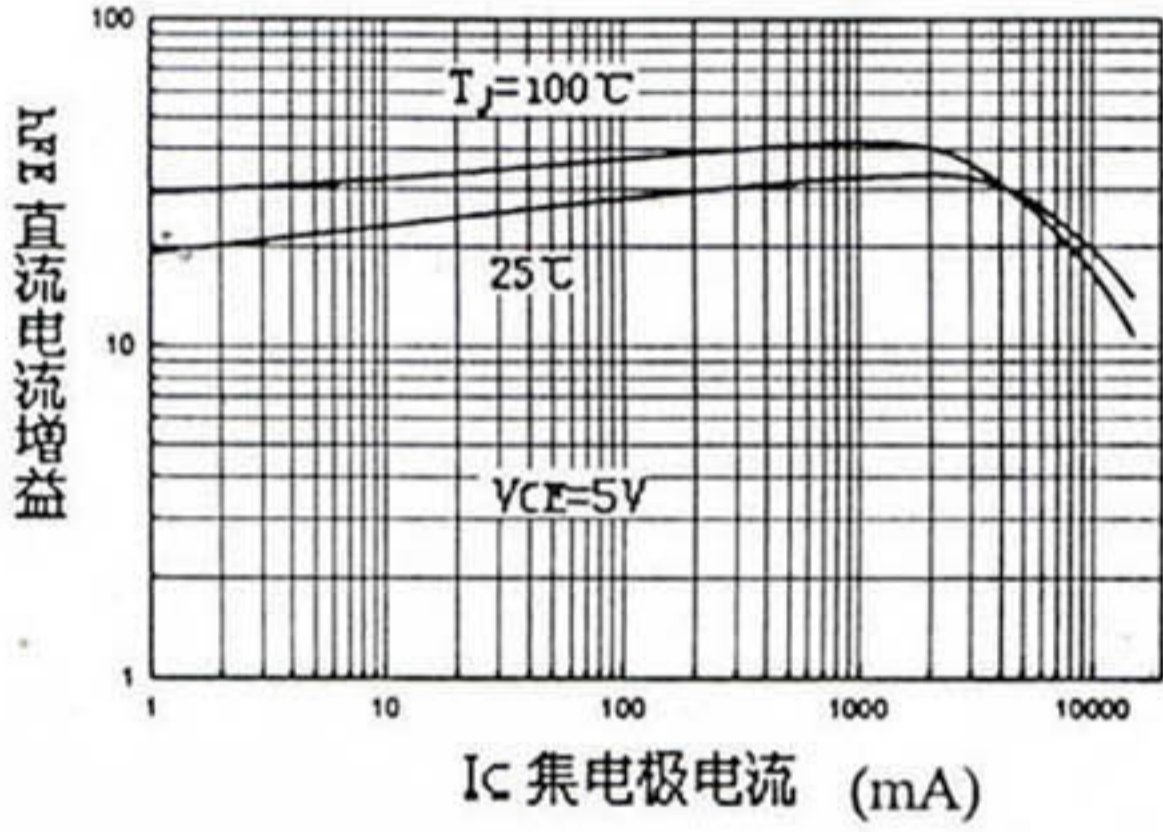
## ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

Characteristic	Symbol	Test conditions	MIN	TYP	MAX	Unit
Collector -base breakdown voltage	V(BR)CBO	Ic=1000μA, IE=0	700			V
*Collector -emitter Sustaining Voltage	V(BR)CEO	Ic=10mA, IB=0	400			V
Emitter cut-off current	IEBO	VEB=9V, IC=0			10	μA
DC current gain	hFE(1)	VCE=5V, IC=2A	15		50	
	hFE(2)	VCE=5V, IC=5A	10			
	hFE(3)	VCE=5V, IC=10A	8			
Collector -emitter saturation voltage	VCE(sat)	IC=10A, IB=2A			1	V
Base-emitter saturation voltage	VBE(sat)	IC=10A, IB=2A			1.5	V
Base Emitter Voltage	VBE(ON)	IE= 2000 mA			3	V
Current Gain Bandwidth Product	fT	VCE=10V, IC=0.5A	4			MHZ
Turn On Time	TON					μs
Storage Time	ts	VCC=24V IC=6A,			3	μs
Fall Time	tf	IB1=-IB2=1.2A			0.7	μs

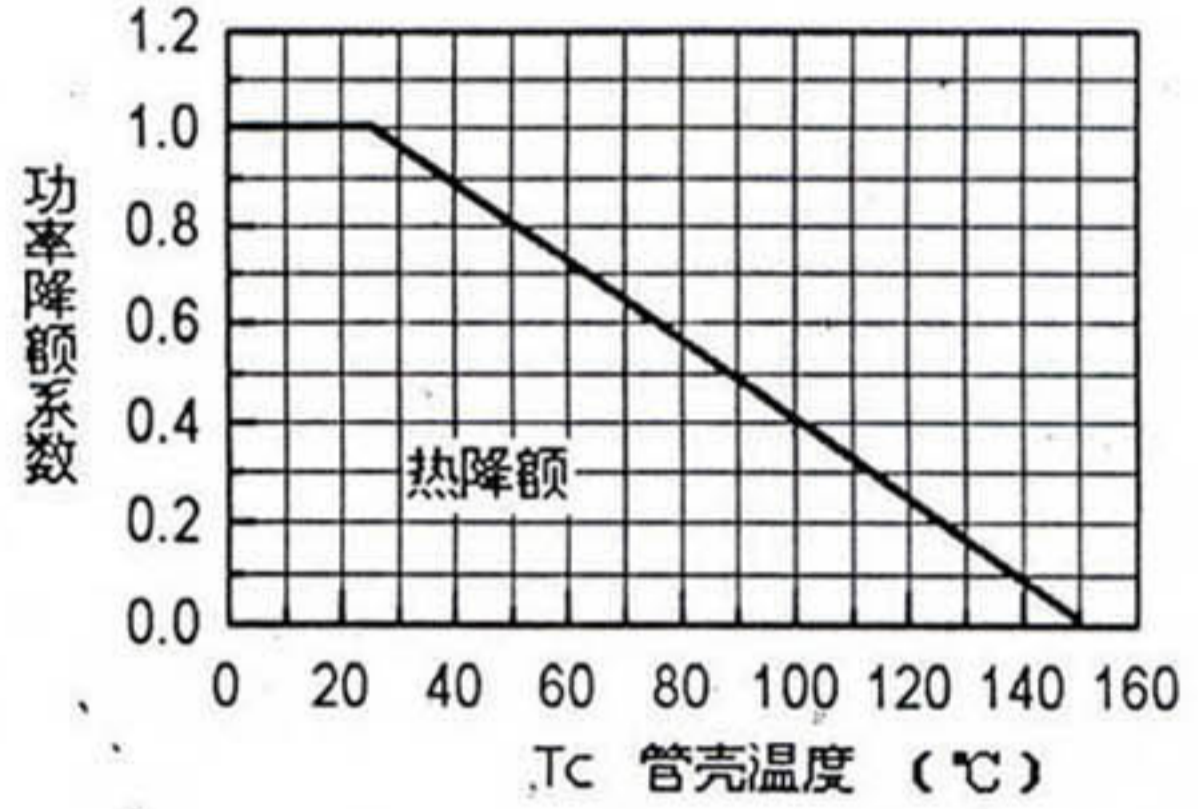
## D4515

### Typical Characteristics

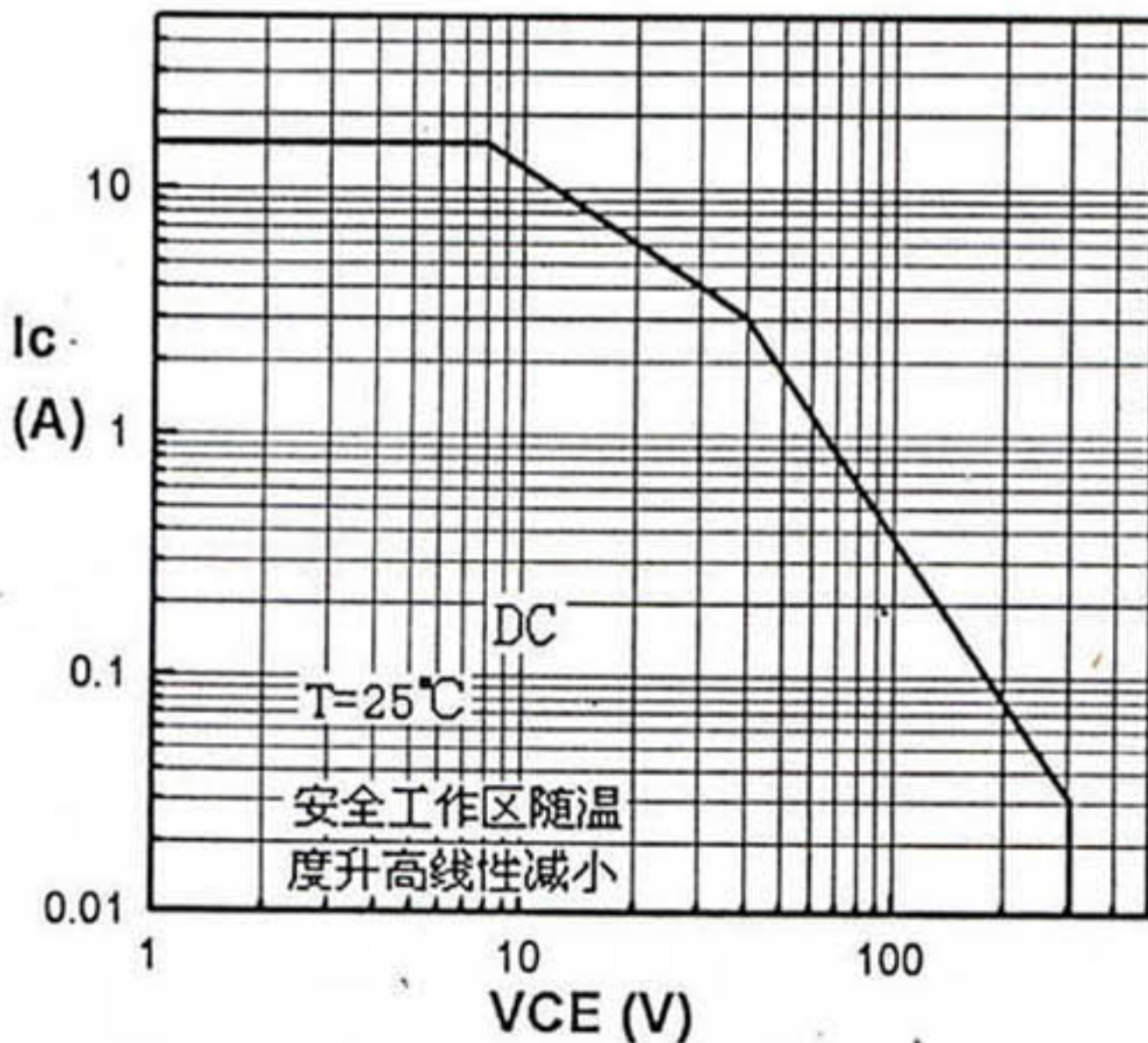
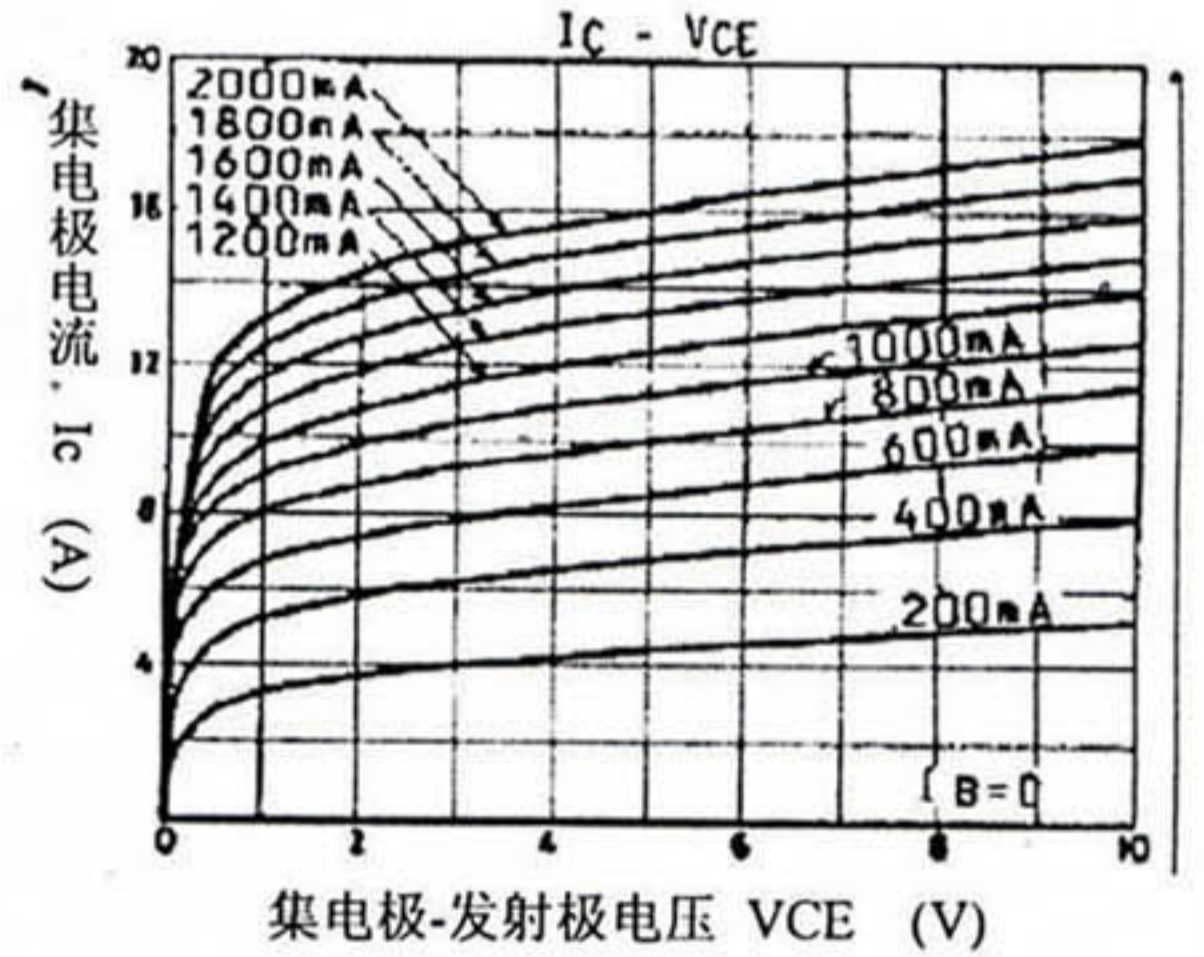
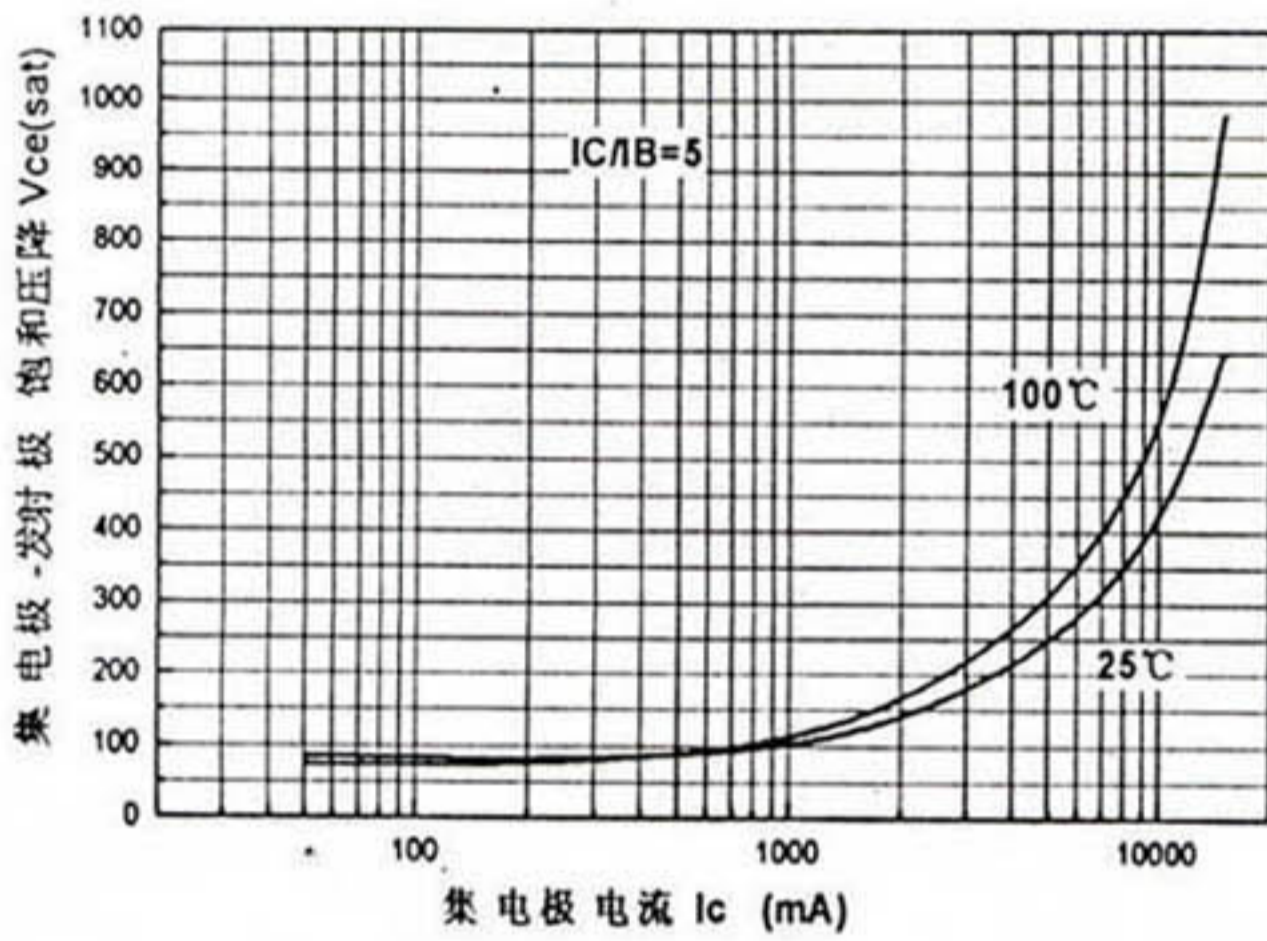
百流增益-集电极电流特性



功率-温度降额特性



饱和压降-集电极电流特性



## T0-3PN 外形尺寸图

单位: mm

### T0-3PN

